## 4V Drive Pch+SBD MOSFET

V <sub>DSS</sub>	-45V
R <sub>DS(on)</sub> (Max.)	800mΩ
I <sub>D</sub>	±0.7A
P <sub>D</sub>	1.0W

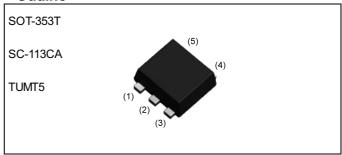
## Features

- 1) The US5U35 combines Pch MOSFET with a Schottky barrier diode in a single
- 2) High-speed switching, Low On-resistance
- 3) Built-in Low V<sub>F</sub> schottky barrier diode
- 4) Pb-free lead plating; RoHS compliant

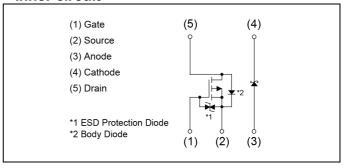
# Application

switching

## Outline



## •Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	180
Туре	Tape width (mm)	8
	Quantity (pcs)	3000
	Taping code	TR
	Marking	U35

# ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

### <MOSFET>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	-45	V
Gate - Source voltage	V <sub>GSS</sub>	±20	V
Continuous drain current	I <sub>D</sub>	±0.7	Α
Pulsed drain current	I <sub>DP</sub> *1	±2.8	А
Continuous source current (body diode)	I <sub>S</sub>	-0.4	А
Pulsed source current (body diode)	I <sub>SP</sub> *1	-2.8	А
Power dissipation	P <sub>D</sub> *3	0.7	W/element
Junction temperature	T <sub>j</sub>	150	°C

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

## <Di>

Parameter	Symbol	Value	Unit	
Repetitive peak reverse voltage	$V_{RM}$	45	V	
Reverse voltage	V <sub>R</sub>	40	V	
Forward current	I <sub>F</sub>	100	mA	
Forward current surge peak	I <sub>FSM</sub> *2	1.0	Α	
Power dissipation	P <sub>D</sub> *3	0.5	W/element	
Junction temperature	T <sub>j</sub>	150	°C	

## <MOSFET + Di>

Parameter	Symbol	Value	Unit
Power dissipation	P <sub>D</sub> *3	1.0	W/total
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	°C

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Daramatar	Cymah ol	Conditions	Values			l leit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μΑ
Drain - Source breakdown voltage	own $V_{(BR)DSS}$ $V_{GS} = 0V, I_D = -1mA$		-45	-	-	٧
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -45V, V <sub>GS</sub> = 0V	-	-	-1	μA
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = -10V, I_{D} = -1mA$	-1.0	-	-2.5	V
		$V_{GS} = -10V, I_D = -0.7A$	-	600	800	
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	$V_{GS} = -4.5V, I_D = -0.7A$	-	900	1300	mΩ
		$V_{GS} = -4.0V, I_D = -0.35A$	-	1000	1400	
Forward Transfer Admittance	Y <sub>fs</sub>  *4	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.7A	0.6	-	-	S



# ● Electrical characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Darameter	Symbol	Conditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	120	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V	-	14	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	11	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq$ -25V, $V_{GS}$ = -10V	-	6	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -0.35A	-	5	-	no
Turn - off delay time	t <sub>d(off)</sub> *4	R <sub>L</sub> = 71Ω	-	17	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	6	-	

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Parameter	Symbol	Conditions	Values			Llait
		Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Qg*4		-	1.7	-	
Gate - Source charge	Q <sub>gs</sub> *4	$V_{DD} \simeq -25V, I_{D} = -0.7A$ $V_{GS} = -5V$	-	0.8	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4		-	0.5	-	

# ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

## <MOSFET>

Parameter	Symbol Conditions	Values			l leit	
		Conditions	Min.	Тур.	Max.	Unit
Forward voltage	$V_{SD}^{*4}$	$V_{GS} = 0V, I_{S} = -0.7A$	-	-	-1.2	V

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

## <Di>

Parameter	Symbol	Conditions	Values			l leit
			Min.	Тур.	Max.	Unit
Forward voltage	$V_{F}$	I <sub>F</sub> = 100mA	-	-	0.55	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 10V	-	-	30	μA

<sup>\*1</sup> Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

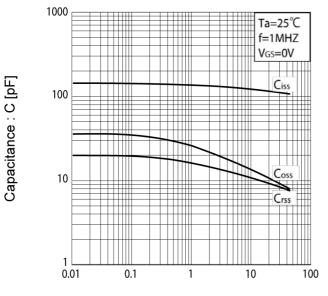
<sup>\*2 60</sup>Hz-1 cycle

<sup>\*3</sup> Mounted on a ceramic boad (30×30×0.8mm)

<sup>\*4</sup> Pulsed

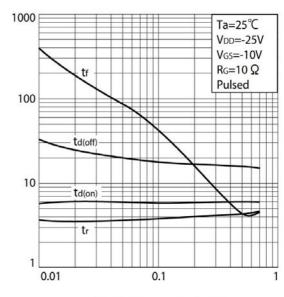
## • Electrical characteristic curves < MOSFET >

Fig.1 Typical Capacitance vs. Drain - Source Voltage



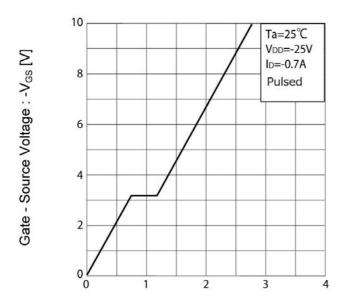
Drain - Source Voltage :  $-V_{DS}[V]$ 

Fig.2 Switching Characteristics



Drain Current : -I<sub>D</sub> [A]

Fig.3 Dynamic Input Characteristics

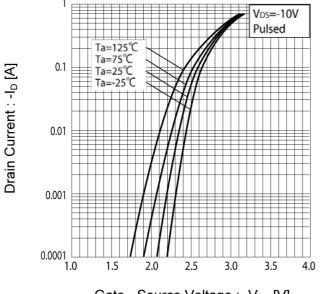


Total Gate Charge : Qg [nC]

Switching Time : t [ns]

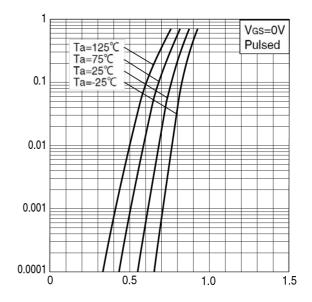
## • Electrical characteristic curves < MOSFET >

Fig.4 Typical Transfer Characteristics



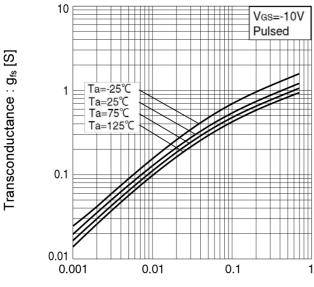
Gate - Source Voltage : -V<sub>GS</sub> [V]

Fig.5 Source Current vs. Source Drain Voltage



Source - Drain Voltage : -V<sub>SD</sub> [V]

Fig.6 Transconductance vs. Drain Current



Source Current : -I<sub>s</sub> [A]

#### • Electrical characteristic curves < MOSFET>

Fig.7 Static Drain - Source On - State Resistance vs. Drain Current (I)

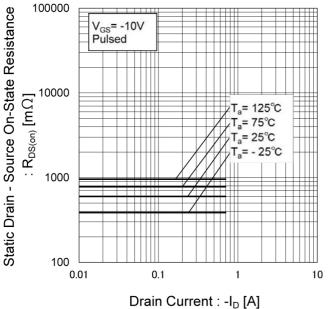
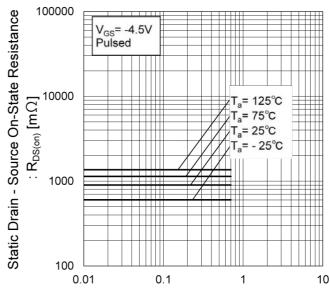
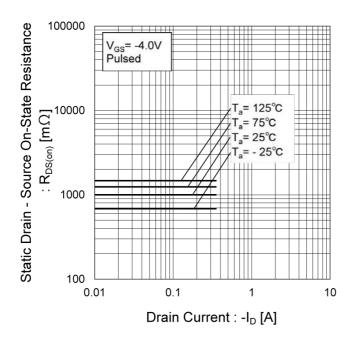


Fig.8 Static Drain - Source On - State Resistance vs. Drain Current (II)



Drain Current: -ID [A]

Fig.9 Static Drain - Source On - State Resistance vs. Drain Current (III)



### ● Electrical characteristic curves < Diode >

Fig.11 Forward Current vs. Forward Voltage

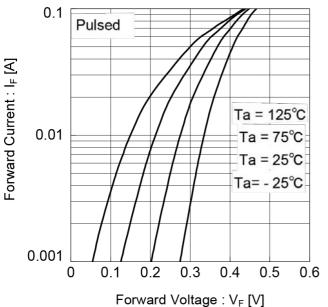
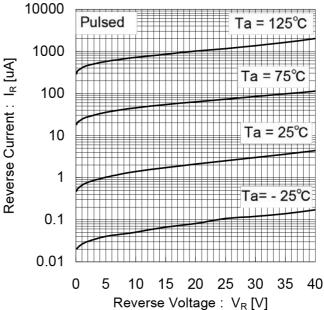


Fig.12 Reverse Current vs. Reverse Voltage



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#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

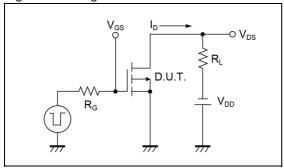


Fig.2-1 Gate Charge Measurement Circuit

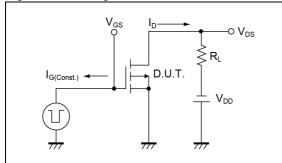


Fig.1-2 Switching Waveforms

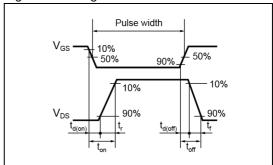
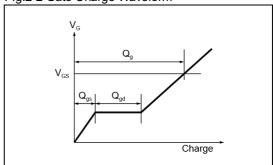


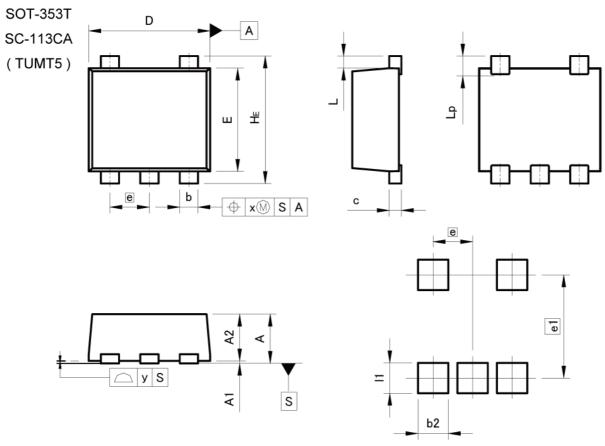
Fig.2-2 Gate Charge Waveform



#### Notice

- SBD has a large reverse leak current compared to other type of diode. Therefore, it would raise a junction temperature, and increase a reverse power loss. Further rise of inside temperature would cause a thermal runaway. This built-in SBD has low V<sub>F</sub> characteristics and therefore, higher leak current. Please consider enough the surrounding temperature, generating heat of MOSFET and the reverse current.
- 2. This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

## Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

DIM -	MILIM	ETERS	INCHES		
DIM [	MIN	MAX	MIN	MAX	
Α	<del>=</del> 0	0.85	<del></del>	0.033	
A1	0.00	0.10	0.000	0.004	
A2	0.72	0.82	0.028	0.032	
b	0.25	0.40	0.010	0.016	
С	0.12	0.22	0.005	0.009	
D	1.90	2.10	0.075	0.083	
E	1.60	1.80	0.063	0.071	
е	0.	65	0.026		
HE	2.00	2.20	0.079	0.087	
L	0.	20	0.0	08	
Lp	221	0.40	72	0.016	
х	*	0.10	9	0.004	
У	<del></del>	0.10	855	0.004	

DIM	MILIME		DIM MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX		
b2	228	0.50	100	0.020		
e1	1.7	1.70		67		
11	₹86	0.50	\$ <del>22</del>	0.020		

Dimension in mm/inches



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JAPAN	USA	EU	CHINA
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CLASSIV		CLASSⅢ	

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  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
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- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
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- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
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For details, please refer to ROHM Mounting specification

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
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- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
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